

**IN THE SPECIFICATION:**

Please replace the paragraph at page 14, lines 12-17 with the following amended paragraph:

By using the tungsten film, in which the amount of sodium contained within the film is equal to or less than ~~[[0.03]]~~ 0.3 ppm, which has a low electrical resistivity (equal to or less than  $40 \mu \Omega \cdot \text{cm}$ ) even after heat treatment, and in which the stress is controlled to be from  $-5 \times 10^{10}$  to  $5 \times 10^{10}$  dyn/cm<sup>2</sup>, as the material for the gate wirings and other wirings of the TFT, the present invention can greatly increase the operating performance and the reliability of a semiconductor device provided with the TFT.

Please replace the paragraph at page 43, line 24 - page 44, line 3 with the following amended paragraph:

By using the present invention, a wiring can be formed in which the amount of sodium contained in the wiring is equal to or less than ~~[[0.03]]~~ 0.3 ppm, preferably equal to or less than ~~[[0.01]]~~ 0.1 ppm, which has a low electrical resistivity (equal to or less than  $40 \mu \Omega \cdot \text{cm}$ ), and in which the stress is controlled to be equal to or greater than  $-5 \times 10^{10}$  dyn/cm<sup>2</sup> and equal to or less than  $5 \times 10^{10}$  dyn/cm<sup>2</sup>.

Please replace the Abstract of the Disclosure with the following amended Abstract of the Disclosure:

A semiconductor device having good TFT characteristics is realized. By using a high purity target as a target, using a single gas, argon (Ar), as a sputtering gas, setting the substrate temperature equal to or less than 300°C, and setting the sputtering gas pressure from 1.0 Pa to 3.0 Pa, the film stress of a film is made from  $-1 \times 10^{10}$  dyn/cm<sup>2</sup> to  $1 \times 10^{10}$  dyn/cm<sup>2</sup>. By thus using a conducting film in

which the amount of sodium contained within the film is equal to or less than ~~[[0.03]]~~ 0.3 ppm, preferably equal to or less than ~~[[0.01]]~~ 0.1 ppm, and having a low electrical resistivity (equal to or less than  $40 \mu \Omega \cdot \text{cm}$ ), as a gate wiring material and a material for other wirings of a TFT, the operating performance and the reliability of a semiconductor device provided with the TFT can be increased.